

2N7002T N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

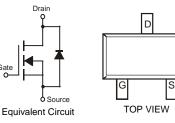
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Notes 3 and 4)

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.002 grams (approximate)







Maximum Ratings @T_A = 25°C unless otherwise specified

Chara	acteristic	Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0M	Ω	V _{DGR}	60	V
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V
Drain Current (Note 1)	Continuous Continuous @ 100°C Pulsed	۱ _D	115 73 800	mA

SOT-523

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	Pd	150	mW
Thermal Resistance, Junction to Ambient	R ₀ JA	833	°C/W
Operating and Storage Temperature Range	Tj, T _{STG}	-55 to +150	°C

1. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our Notes: website at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.

3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

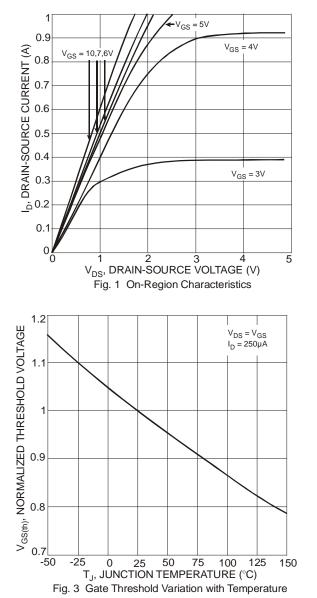
4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

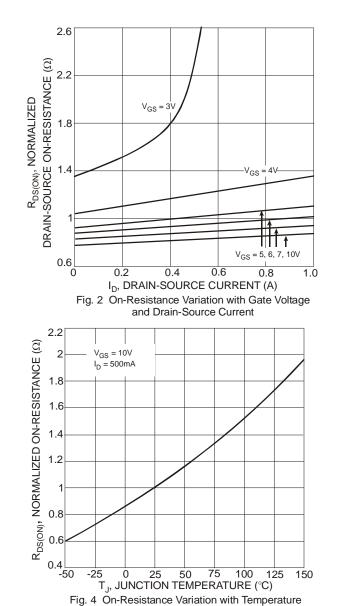


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)							·
Drain-Source Breakdown Voltage		BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}	_	_	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage		V _{GS(th)}	1.0	_	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _j = 25°C @ T _i = 125°C	R _{DS (ON)}		2.0 4.4	7.5 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g _{FS}	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS							·
Input Capacitance		Ciss	_	22	50	pF	
Output Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}	_	2.0	5.0	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}		7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(OFF)}		11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

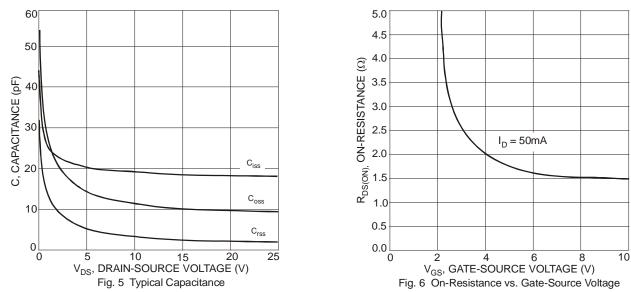
Notes: 5. Short duration pulse test used to minimize self-heating effect.







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Ordering Information (Note 6)

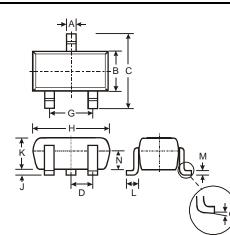
Part Number	Case	Packaging
2N7002T-7-F	SOT-523	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

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			7	72 YN	Л Ү Ү	2 = Produc M = Date (= Year (ex 1 = Month (Code Marki c: T = 2006	ng))			
Date Code Key												
Year	2005		2006	2007		2008	2009		2010	2011		2012
Code	S		Т	U		V	W		Х	Y		Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

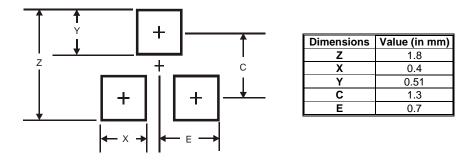
Package Outline Dimensions



SOT-523							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
С	1.45	1.75	1.60				
D			0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
J	0.00	0.10	0.05				
К	0.60	0.80	0.75				
L	0.10	0.30	0.22				
М	0.10	0.20	0.12				
N	0.45	0.65	0.50				
α	0°	8°					
All Dimensions in mm							



Suggested Pad Layout



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